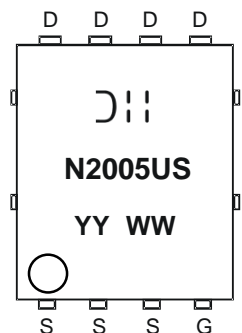


## Marking Information



D = Manufacturer's Marking  
 N2005US = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 20 = 2020)  
 WW = Week Code (01 to 53)

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	20	A
		T <sub>A</sub> = +70°C		15	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>C</sub> = +25°C	I <sub>D</sub>	100	A
		T <sub>C</sub> = +70°C		88	
Pulsed Drain Current (380μs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	150	A
Maximum Continuous Body Diode Forward Current (Mounted on Infinite Heatsink)			I <sub>S</sub>	150	A
Avalanche Current (Note 7) L=0.2mH			I <sub>AS</sub>	36	A
Avalanche Energy (Note 7) L=0.2mH			E <sub>AS</sub>	133	mJ

## Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P <sub>D</sub>	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R <sub>θJA</sub>	98	°C/W
	t<10s		83	
Total Power Dissipation (Note 6)		P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R <sub>θJA</sub>	51	°C/W
	t<10s		43	
Thermal Resistance, Junction to Case		R <sub>θJC</sub>	1.5	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.  
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.  
 7. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.4	0.7	1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	4.6	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 13.5A
		—	—	8.7		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 13.5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 27A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	5337	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	560	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	505	—	pF	
Gate Resistance	R <sub>g</sub>	—	0.7	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	60	—	nC	V <sub>DS</sub> = 16V, I <sub>D</sub> = 27A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	142	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	7	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	11	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	12.4	—	ns	V <sub>GS</sub> = 5V, V <sub>DS</sub> = 10V, R <sub>G</sub> = 4.7Ω, I <sub>D</sub> = 13.5A
Turn-On Rise Time	t <sub>r</sub>	—	29.8	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	117	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	52	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	17.8	—	ns	I <sub>F</sub> = 13.5A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	8.6	—	nC	I <sub>F</sub> = 13.5A, di/dt = 100A/μs

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

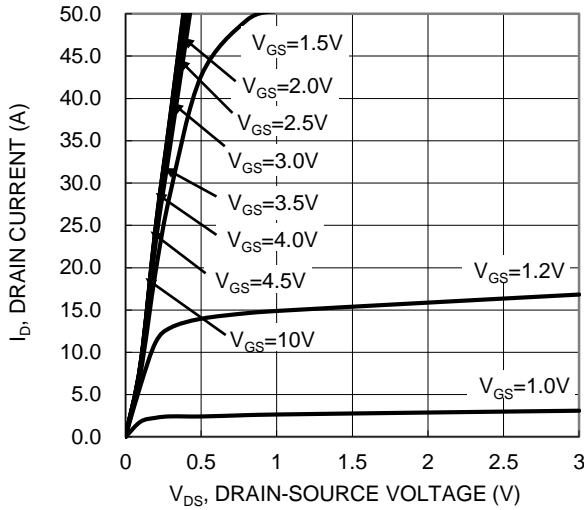


Figure 1. Typical Output Characteristic

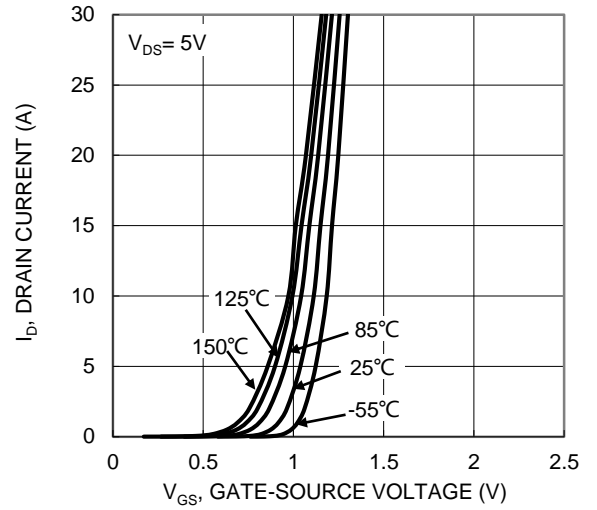


Figure 2. Typical Transfer Characteristic

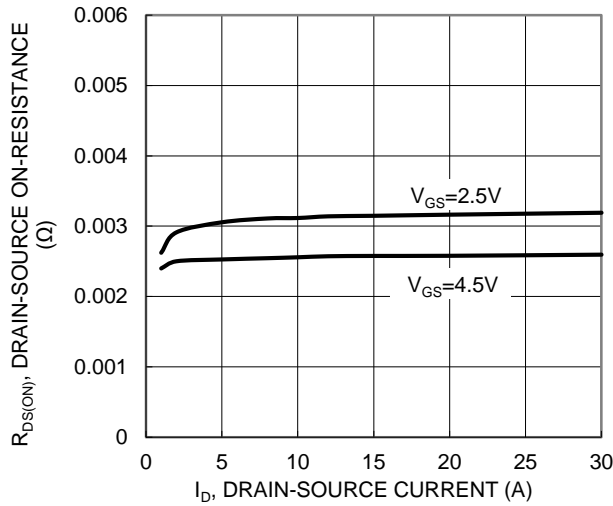


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

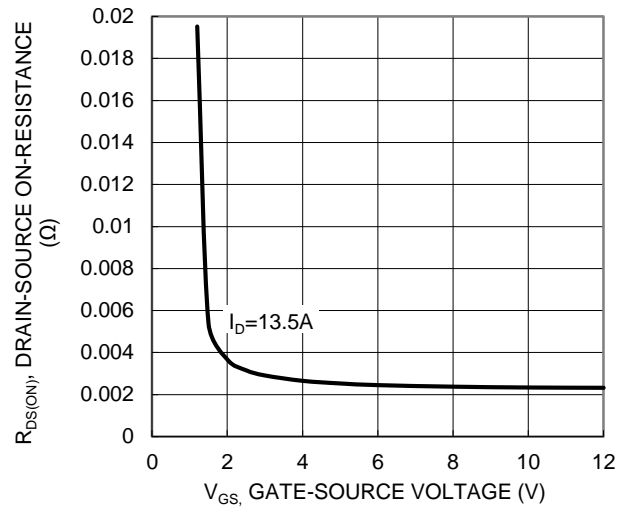


Figure 4. Typical Transfer Characteristic

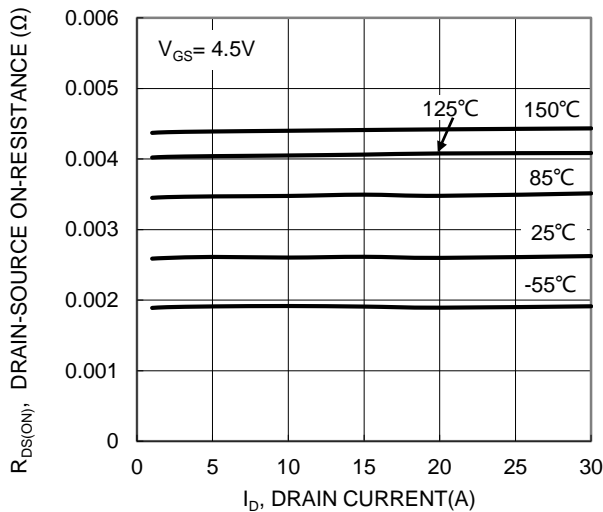


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

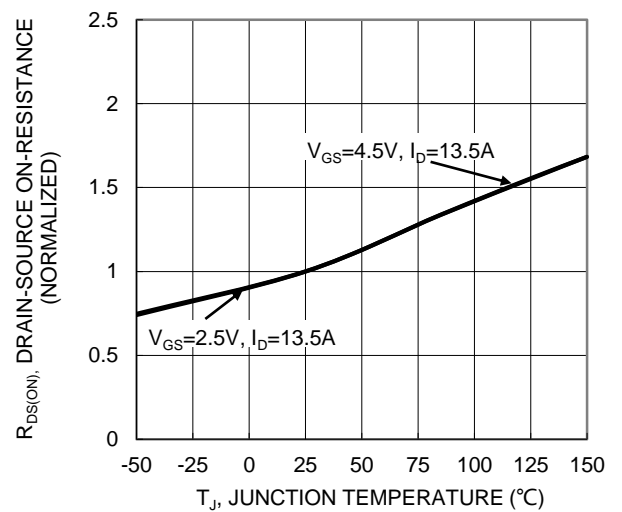


Figure 6. On-Resistance Variation with Junction Temperature

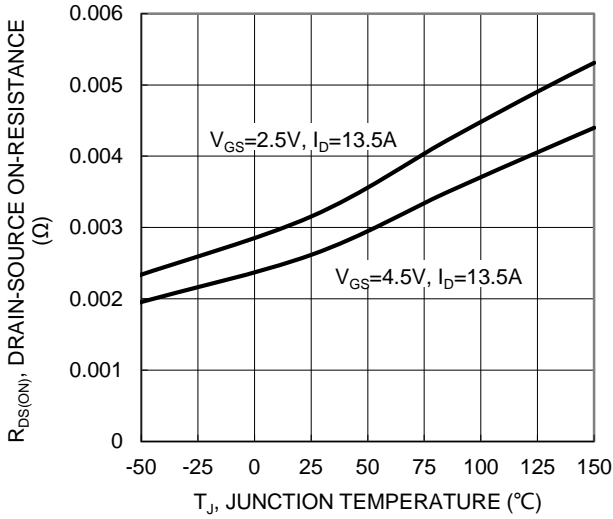


Figure 7. On-Resistance Variation with Junction Temperature

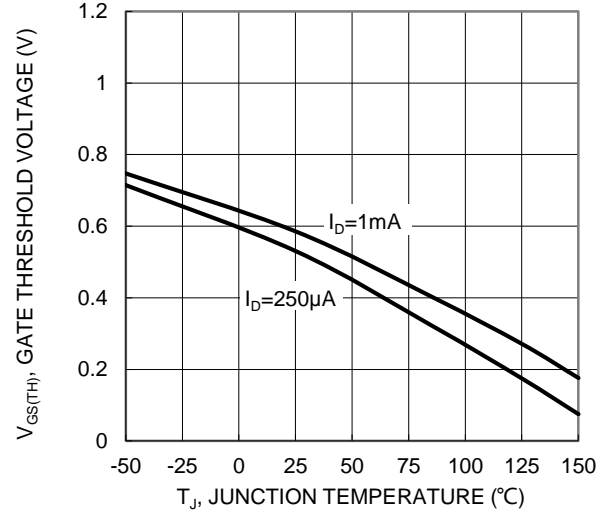


Figure 8. Gate Threshold Variation vs. Junction Temperature

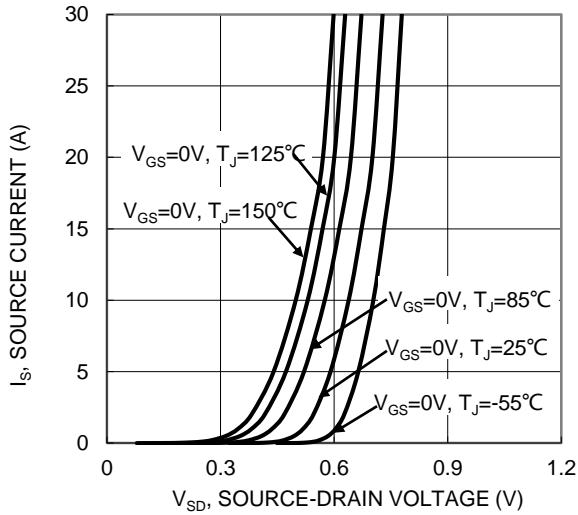


Figure 9. Diode Forward Voltage vs. Current

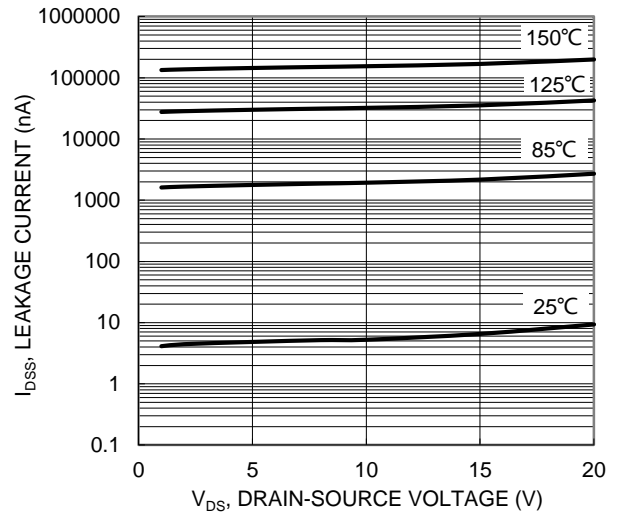


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

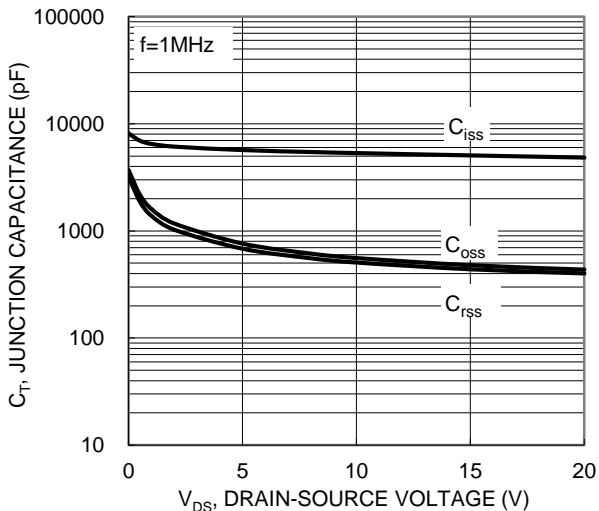


Figure 11. Typical Junction Capacitance

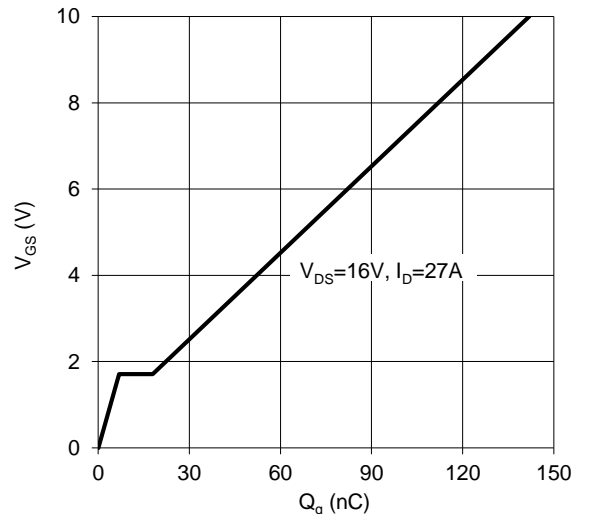
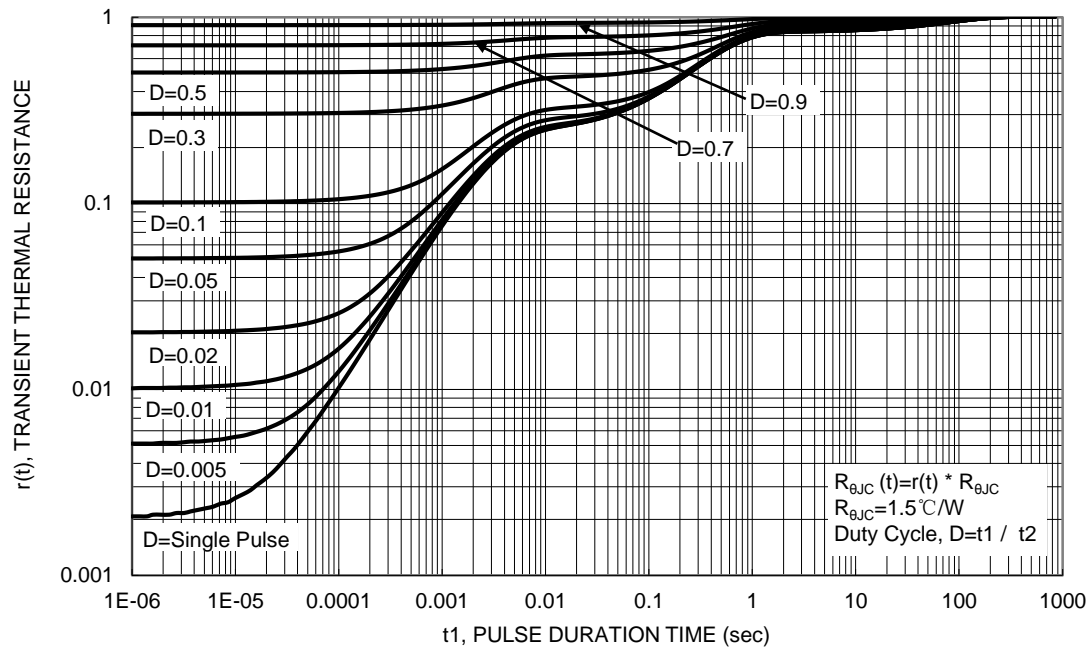
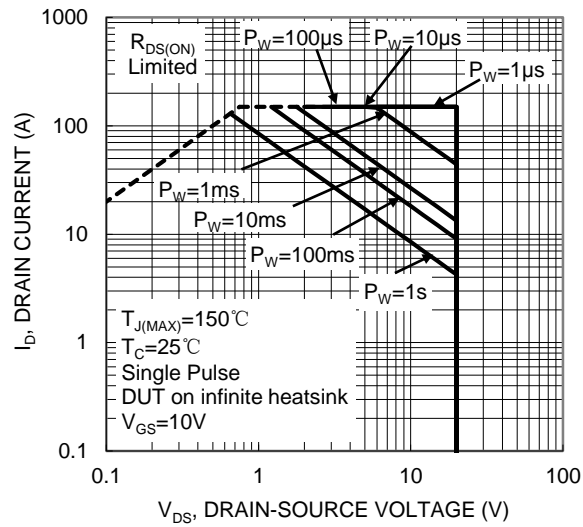


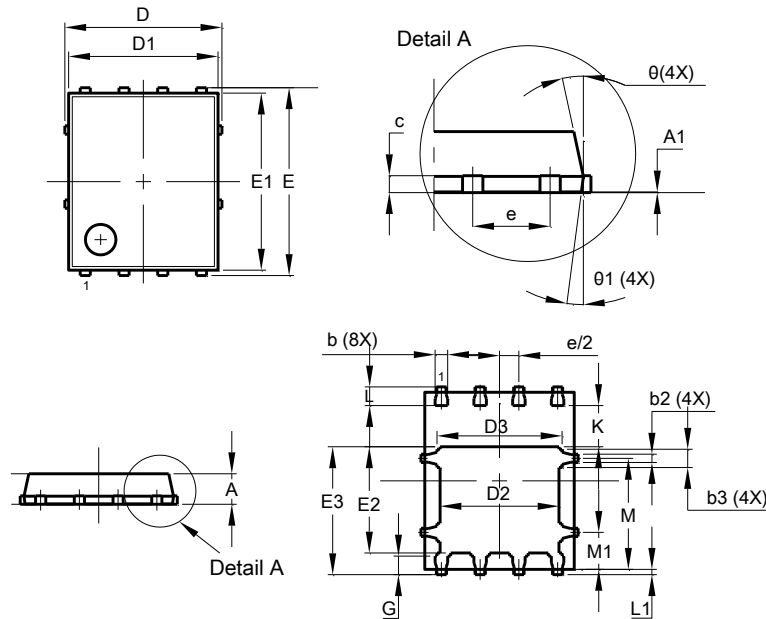
Figure 12. Gate Charge



## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8

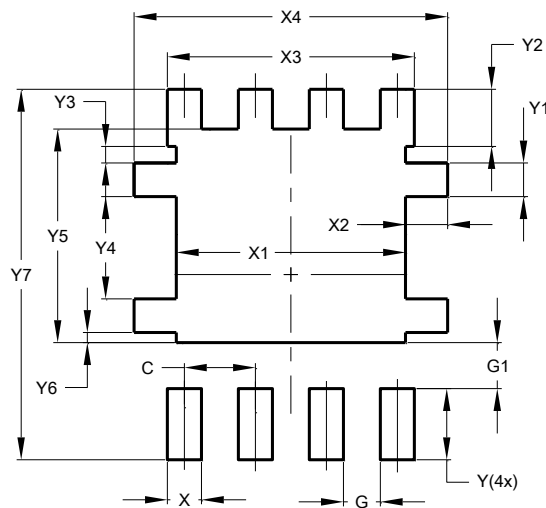


PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
$\theta$	10°	12°	11°
$\theta1$	6°	8°	7°
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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